MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TPH7R204PL

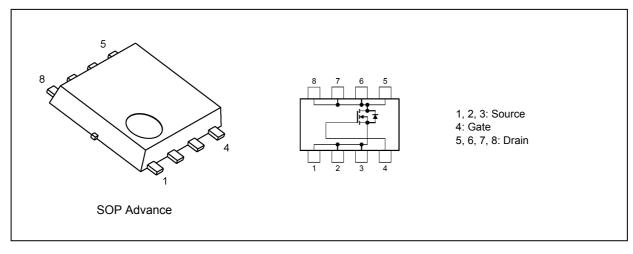
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 6.0 \text{ nC}$ (typ.)
- (3) Small output charge: $Q_{oss} = 16 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 5.4 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (5) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- (6) Enhancement mode: V_{th} = 1.4 to 2.4 V (V_{DS} = 10 V, I_D = 0.2 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	40	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	Ι _D	48	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι _D	72	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	150	
Power dissipation	(T _c = 25 °C)		PD	69	×
Power dissipation		(Note 3)	PD	1.8	
Power dissipation		(Note 4)	PD	0.83	
Single-pulse avalanche energy		(Note 5)	E _{AS}	13	mJ
Single-pulse avalanche current		(Note 5)	I _{AS}	48	A
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	2.15	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	83	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	180	

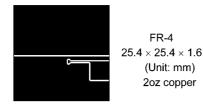
Note 1: Ensure that the channel temperature does not exceed 175 °C.

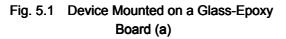
Note 2: Limited 48 A by package capability.

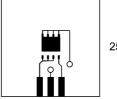
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_DD = 32 V, T_ch = 25 °C (initial), L = 4.5 $\mu H, \, I_{AS}$ = 48 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	—	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	40	_	_	V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	25	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.2 mA	1.4	_	2.4	1
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 15 A	_	6.9	9.7	mΩ
		V _{GS} = 10 V, I _D = 24 A	_	5.4	7.2	

Note 6: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	_	1570	2040	pF
Reverse transfer capacitance	C _{rss}		_	35	70	
Output capacitance	C _{oss}		_	380	_	
Gate resistance	r _g	—	—	0.9	1.4	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	5.6	—	ns
Switching time (turn-on time)	t _{on}		_	14	_	
Switching time (fall time)	t _f]		7.3	_	
Switching time (turn-off time)	t _{off}			25	_	

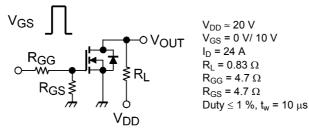


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

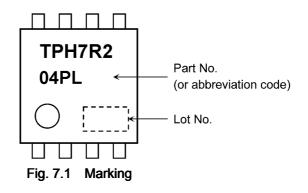
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx 20~V,~V_{GS}$ = 10 V, I _D = 24 A	_	24	_	nC
gate-drain)		$V_{DD} \approx 20$ V, V_{GS} = 4.5 V, I_D = 24 A	_	12	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 20$ V, V_{GS} = 10 V, I_D = 24 A	_	5.0	_	
Gate-drain charge	Q _{gd}		_	4.0	_	
Gate switch charge	Q _{SW}		—	6.0	_	
Output charge	Q _{oss}	V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz		16		

6.4. Source-Drain Characteristics (T_a = 25 $^{\circ}$ C unless otherwise specified)

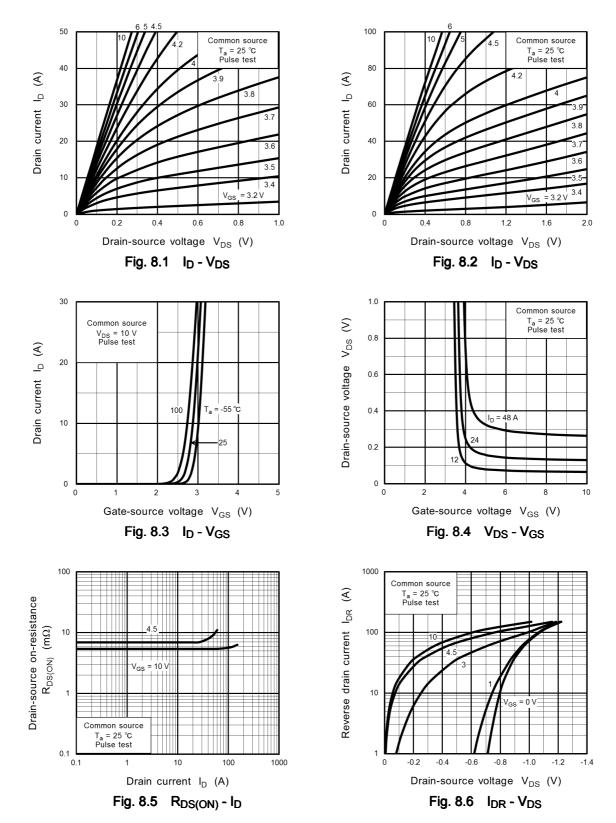
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I _{DRP}	(t = 100 μs)	_	_	150	А
Diode forward voltage	V _{DSF}	I _{DR} = 48 A, V _{GS} = 0 V	_	—	-1.2	V
Reverse recovery time	t _{rr}	I _{DR} = 12 A, V _{GS} = 0 V,	_	25	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/µs	—	15	_	nC

Note 7: Ensure that the channel temperature does not exceed 175 °C.

7. Marking



8. Characteristics Curves (Note)



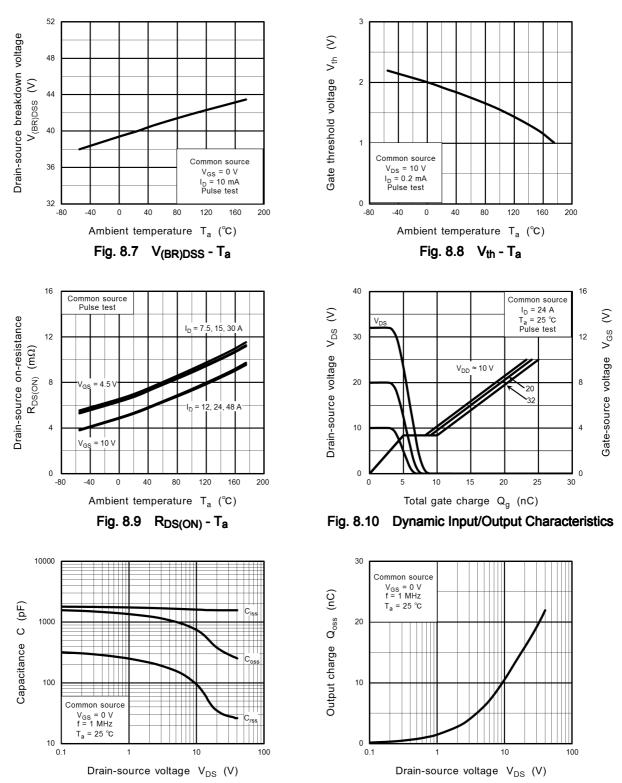
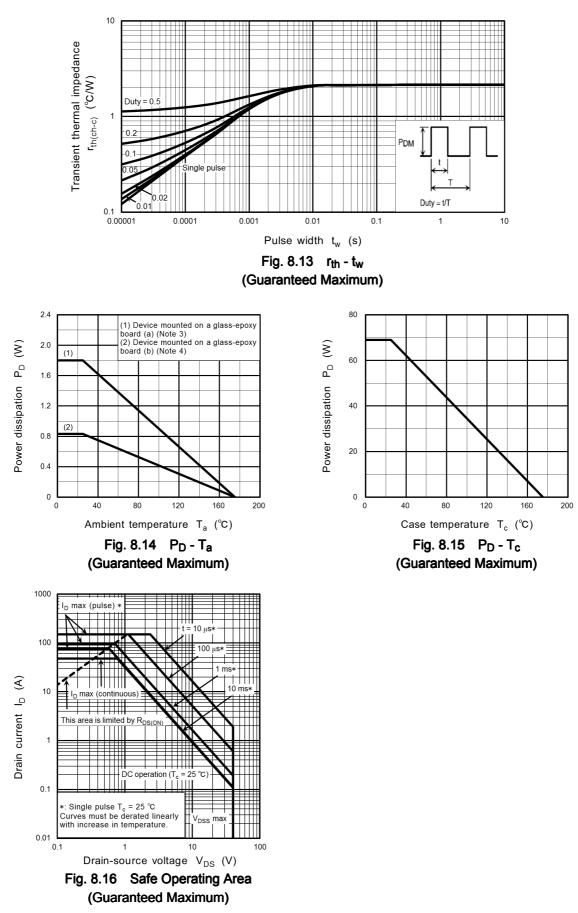


Fig. 8.11 Capacitance - V_{DS}

Fig. 8.12 Qoss - VDS



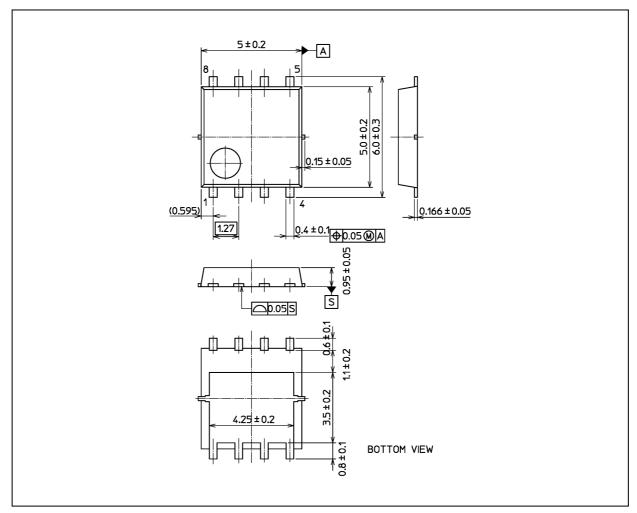
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPH7R204PL

Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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